## **APPLICATION DATA SHEET**

Electronic Version 0.0.11

Stylesheet Version: 1.0

Attorney Docket Number: NAUP0504USA

Publication Filing Type:

new-utility

Application Type:

utility

Title of Invention:

METHOD OF PREVENTING LEAKAGE CURRENT OF A METAL-OXIDE

SEMICONDUCTOR TRANSISTOR

**Customer Number Attorney:** 

027765

**Customer Number Correspondence Address:** 

027765

Continuity Data:

This application is a continuation in part of 09/683,691 2002-02-04 US pending

Foreign Priority:

09/683,691

US 2002-02-04

Priority Claimed

INVENTOR(s):

Primary Citizenship:

R.O.C.

Given Name:

Ming-Sheng

Family Name:

Yang

Residence City:

Hsin-Chu City

**Residence Country:** 

TW

Address:

5F, No. 10, Lane 165, Chung-Hsiao Rd., Hsin-Chu City,

Taiwan, R.O.C.

Hsin-Chu City, TW

Primary Citizenship:

R.O.C.

Given Name:

Chia-Hung

Family Name:

Kao

Residence City:

Tai-Nan City

Residence Country:

TW

Address:

No. 43, Lane 133, Sec. 1, Chien-Kang Rd., Tai-Nan City,

Taiwan, R.O.C.

Tai-Nan City, TW

Primary Citizenship:

R.O.C.

Given Name:

Chin-Cheng

Family Name:

Chien

**Residence City:** 

Chia-Yi Hsien

Residence Country:

TW

Address:

Nei-Pu No. 27, Community 2, She-Kuo Tsun, Chung-Pu

Hsiang, Chia-Yi Hsien, Taiwan, R.O.C.

Chia-Yi Hsien, TW